# 800-900 MHz +<u>38"部路##2P6機座商</u>GaAs FET

August 2006 - Rev 03-Aug-06

### Features

- **High Gain**
- □ +36 dBm Power Output
- Proprietary Power FET Process
- □ >45% Linear Power Added Efficiency
- □ +33 dBm with 30 dBc Third Order Products

#### **Applications**

- □ ISM Band Base Stations
- **Cellular Base Stations**
- □ Wireless Local Loop

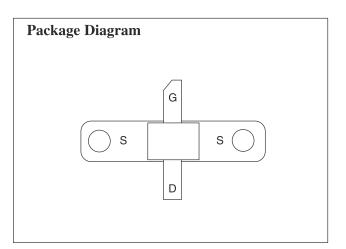
### Description

The CFH2162-P1 is a high-gain, linear FET intended for driver amplifier applications in high-power systems, and output stage usage in medium power applications at power levels up to +36 dBm. The device is easily matched and pro-

**Specifications** (TA =  $25^{\circ}$ C) The following specifications are guaranteed at room temperature in Celeritek test fixture at 850 MHz.

Parameters	Conditions	Min	Тур	Max	Units
$V_d = 10V$ , $I_d = 1100$ mA (Quiescent)					
P <sub>-1dB</sub>		36.0	37.0		dBm
G <sub>-1 dB</sub>		19.0	20.0		dB
<b>3rd Order</b> <b>Products</b> <sup>(1)</sup>		30	35		dBc
Efficiency	@ P1dB		45		%
$\overline{V_d} = 8V, I_d = 1300 \text{ mA (Quiescent)}$					
P <sub>-1dB</sub>		_	36.0		dBm
G <sub>-1 dB</sub>		-	19.0	_	dB

Parameters	Conditions	Min	Тур	Max	Units
g <sub>m</sub>	Vds = 2.0V, Vgs = 0V	—	1700	—	mS
Idss	Vds = 2.0V, Vgs = 0V	—	2.8	—	A
Vp	Vds = 3.0V, Ids = 65 mA	—	-1.8		Volts
BVGD	Igd = 6.5 mA	20	24	_	Volts
$\Theta_{JL}(2)$	@150°C TCH	—	8	—	°C/W



vides excellent linearity at 4 Watts. Manufactured in Celeritek's proprietary power FET process, this device is assembled in a power flange package.

### **Absolute Maximum Ratings**

Parameter	Symbol	Rating
Drain-Source Voltage	V <sub>DS</sub>	15V <sup>(3)</sup>
Gate-Source Voltage	V <sub>GS</sub>	-5V
Drain Current	IDS	Idss
Continuous Dissipation	PT	10W
Channel Temperature	TCH	175°C
Storage Temperature	T <sub>STG</sub>	-65°C to +175°C

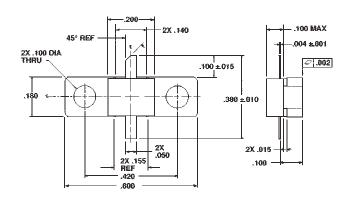
Notes:

1. Sum to two tones with 1 MHz spacing = 33 dBm.

2. See thermal considerations information.

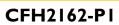
3. Maximum potential difference across the device (Vd + Vg) cannot exceed 18V.

#### **Power Flange Package Physical Dimensions**



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**BROADBAND** 

Mimix

# 800-900 MHz +<u>36" (日日) 112 Politike</u> GaAs FET

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### **Ordering Information**

The CFH2162-P1 power stage is available in a SOIC-8 surface mount package. Devices are available in tape and reel. Ordering part numbers are listed.

Part Number for Ordering CFH2162-P1 <u>Function</u> 800 - 900 MHz Power Stage Package Power flange package

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